

N-Channel Power MOSFET

800V, 4A, 3.0Ω

FEATURES

- Low R_{DS(ON)} 3Ω (Max.)
- Low gate charge typical @ 20nC (Typ.)

TO-220

• Improve dV/dt capability

KEY PERFORMANCE PARAMETERS				
PARAMETER	VALUE UNIT			
V _{DS}	800	V		
R _{DS(on)} (max)	3.0	Ω		
Qg	20	nC		



- Power Supply
- Lighting



ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER	SYMBOL	TO-220	ITO-220	UNIT	
Drain-Source Voltage	V _{DS}	800		V	
Gate-Source Voltage	V _{GS}	±30		V	
Continuous Drain Current (Note 4) $T_{\rm C} = 25^{\circ}{\rm C}$		4		A	
$T_{\rm C} = 100^{\circ}{\rm C}$	Ι _D	2.5			
Pulsed Drain Current (Note 2)	I _{DM}	16		А	
Total Power Dissipation @ $T_c = 25^{\circ}C$	P _{DTOT}	123	38.7	W	
Single Pulsed Avalanche Energy (Note 3)	E _{AS}	7	6	mJ	
Single Pulsed Avalanche Current (Note 3)	I _{AS}	4	4	А	
Repetitive Avalanche Energy	E _{AR}	12	2.3	mJ	
Peak Diode Recovery ^(Note 7)	dV/dt	4	.5	V	
Operating Junction and Storage Temperature Range	T_J,T_STG	- 55 to	o +150	°C	

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	TO-220	ITO-220	UNIT	
Junction to Case Thermal Resistance	$R_{\Theta JC}$	1.01	3.23	°C/W	
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	62.5		°C/W	

Notes: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JA}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. $R_{\Theta JA}$ shown below for single device operation on FR-4 PCB in still air.



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ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	800			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	V _{GS(TH)}	2.0		4.0	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 700 V, V_{GS} = 0 V$	I _{DSS}		🔺	10	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 1.2A$	R _{DS(on)}		2.5	3.0	Ω
Forward Transconductance	$V_{DS} = 30V, I_{D} = 1.2A$	g _{fs}		7.1	_	S
Dynamic ^(Note 5)						
Total Gate Charge		Qg	(20		
Gate-Source Charge	$V_{DS} = 640V, I_D = 4.0A,$ $V_{GS} = 10V$	Q _{gs}		3.7		nC
Gate-Drain Charge		Q _{gd}	-7	8.2		
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	C _{iss}		955		
Output Capacitance		C _{oss}		80		pF
Reverse Transfer Capacitance		C _{rss}		13		
Gate Resistance	F = 1MHz, open drain	Rg			3	Ω
Switching (Note 6)						
Turn-On Delay Time		t _{d(on)}		49		
Turn-On Rise Time	$V_{DD} = 400V,$	t _r		38		
Turn-Off Delay Time	R _{GEN} = 25Ω, I _D = 4.0A, V _{GS} = 10V,	t _{d(off)}		146		ns
Turn-Off Fall Time		t _f		50		
Source-Drain Diode (Note 4)						
Forward On Voltage	I _S = 4.0A, V _{GS} = 0V	V _{SD}			1.5	V
Reverse Recovery Time	$V_{GS} = 0V, I_{S} = 4A$	t _{rr}		487		ns
Reverse Recovery Charge	dl _F /dt = 100A/µs	Q _{rr}		2.8		μC

Notes:

1. Current limited by package

2. Pulse width limited by the maximum junction temperature

- 3. L = 10mH, I_{AS} = 4.0A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25^oC
- 4. Pulse test: $PW \le 300\mu s$, duty cycle $\le 2\%$
- 5. For DESIGN AID ONLY, not subject to production testing.
- 6. Switching time is essentially independent of operating temperature.
- 7. $I_{SD} \le 8A$, dI/dt $\le 200A/uS$, Vdd $\le BV_{DSS}$, Starting $T_J = 25^{\circ}C$.



ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM4N80CZ C0G	TO-220	50pcs / Tube
TSM4N80CI C0G	ITO-220	50pcs / Tube

Note:

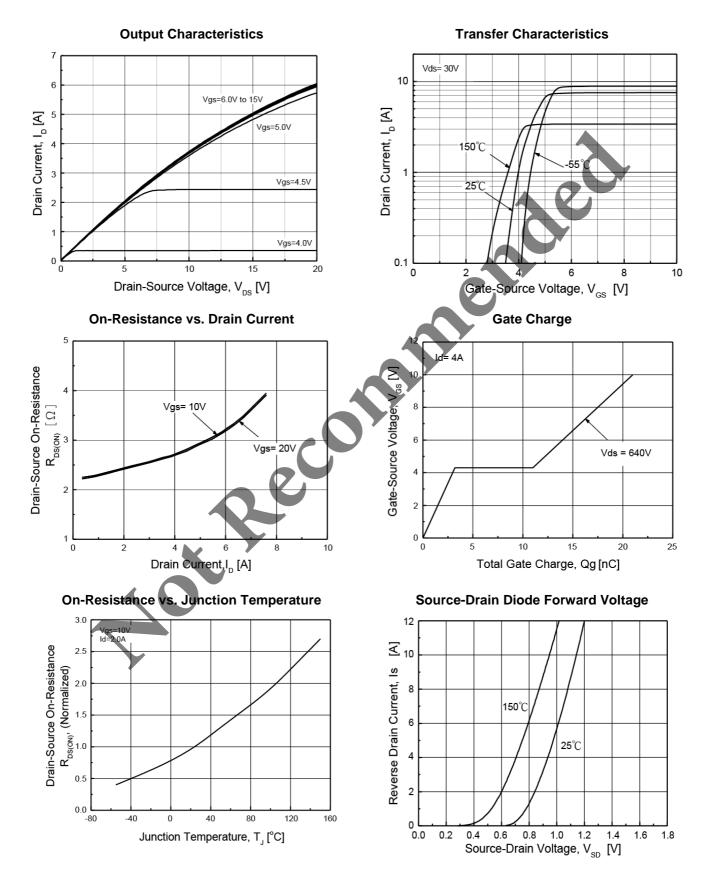
the company of the contract Compliant to RoHS Directive 2011/65/EU and in accordance to WEEE 2002/96/EC 1.

2. Halogen-free according to IEC 61249-2-21 definition



CHARACTERISTICS CURVES

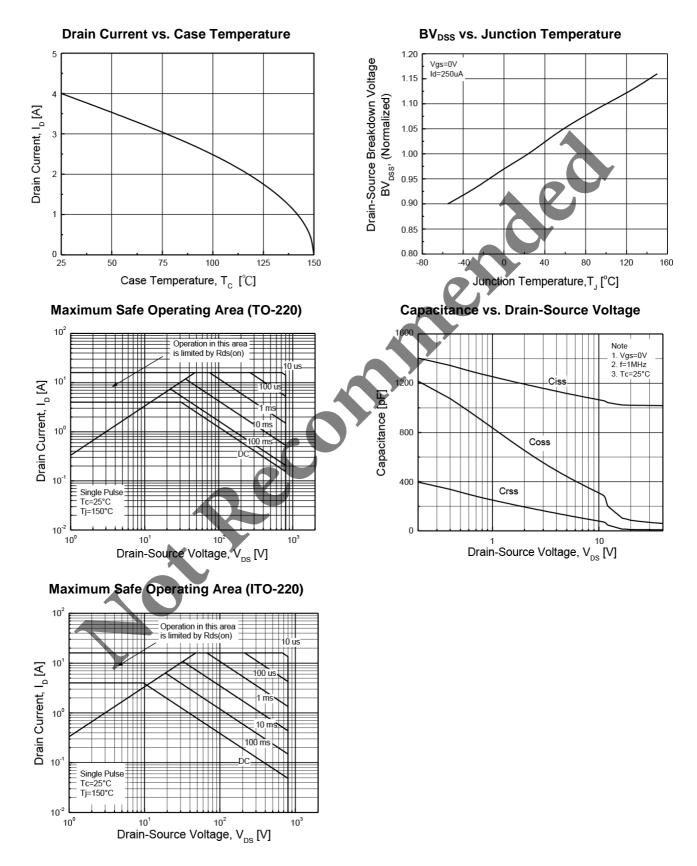
 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$





CHARACTERISTICS CURVES

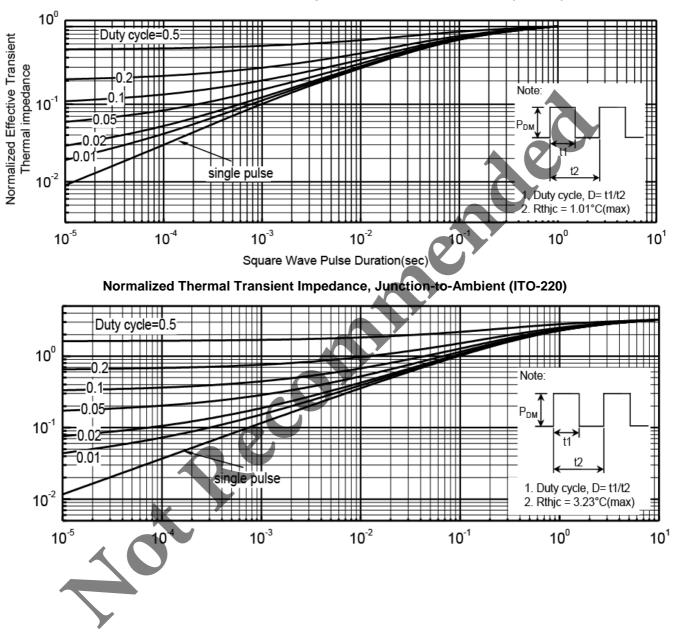
 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$





CHARACTERISTICS CURVES

 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$



Normalized Thermal Transient Impedance, Junction-to-Ambient (TO-220)

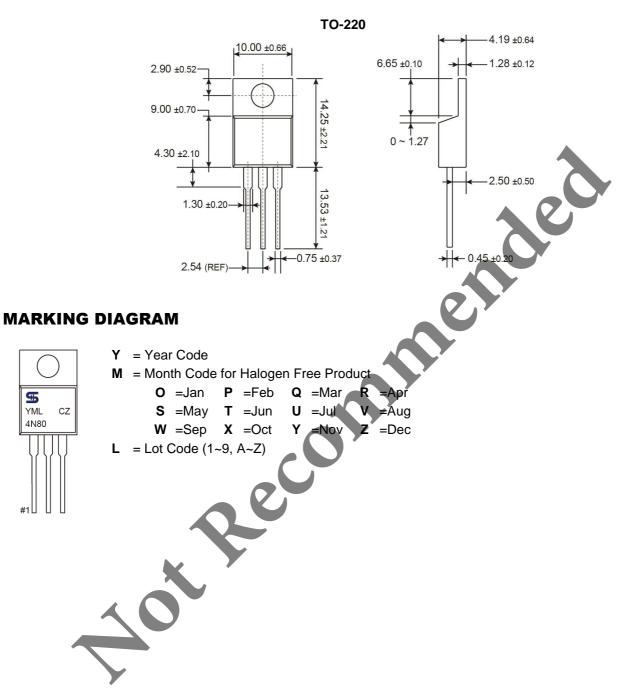




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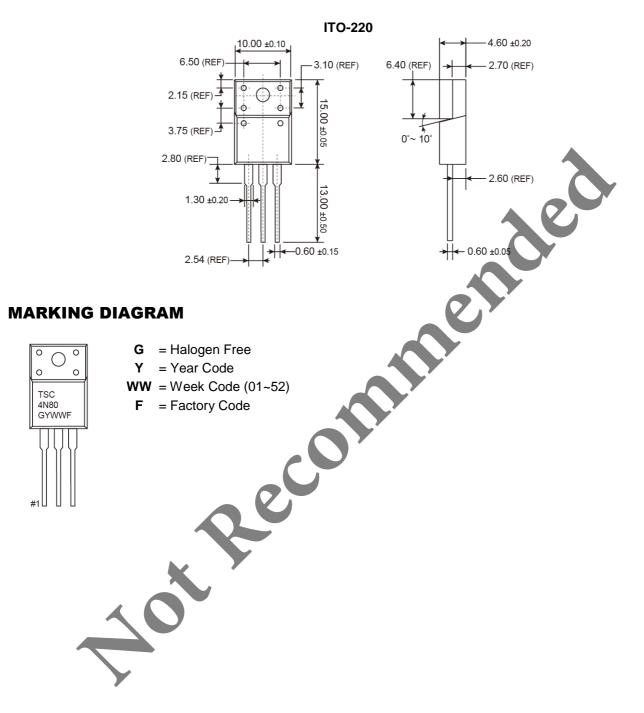




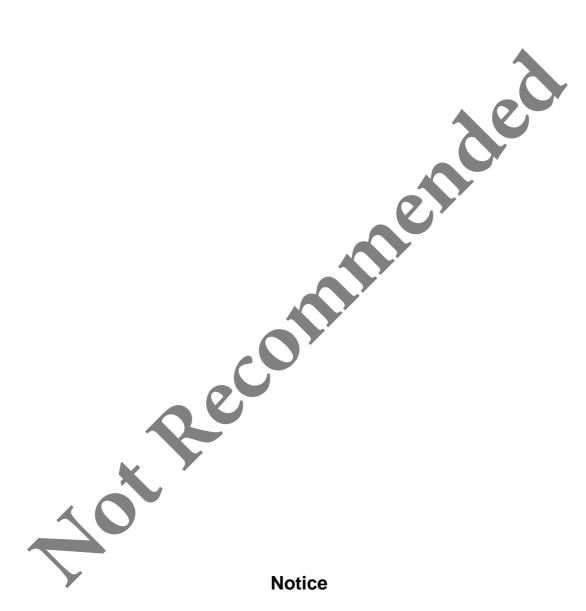


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PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)







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